Form PTO-1449					ATTY. DOCKET NO. 0171-1058P	APPLICATION NO. NEW					
INFORMATION DISCLOSURE CITATION				APPLICANT UNTO VEVAMO TUD OF 3							
IN AN APPLICATION HATAKEYAMA, Jun et al											
(Use several sheets if necessary)					January 29, 200	January 29, 2004					
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SJL	JР	2-27660	B2	1990-06-19	JAPAN	<u>†                                      </u>		ABS			
	JР	63-27829	A	1988-02-05	JAPAN	<del>                                     </del>		ABS			
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